

ABSTRACT

SiC WAFER PRODUCING METHOD

Disclosed herein is an SiC wafer producing method for producing an SiC wafer from a single crystal SiC ingot. The SiC wafer producing method includes a wafer producing step of separating a part of the ingot along a separation layer as an interface. The wafer producing step includes the steps of immersing the ingot in a liquid and applying the ultrasonic wave from an ultrasonic vibrator through the liquid to the ingot, the ultrasonic wave having a frequency greater than or equal to a critical frequency close to the natural frequency of the ingot.

(Figure 6A)